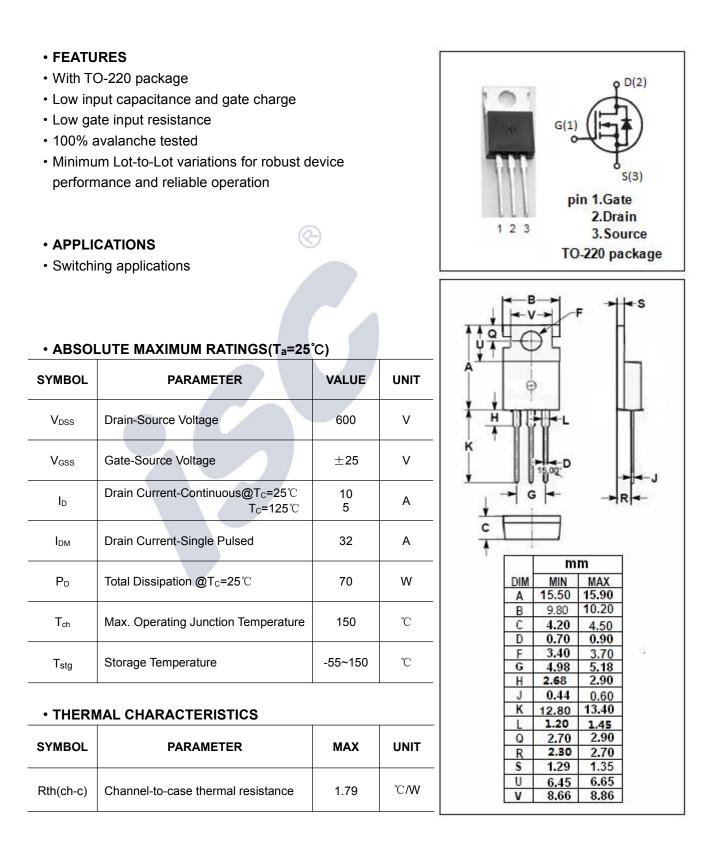


Isc N-Channel MOSFET Transistor

STP10NM60N



isc website: www.iscsemi.cn

isc & iscsemi is registered trademark

1



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STP10NM60N

ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	600			v
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} = ±25V; I _D =0.25mA	2		4	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =4A		60	65	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±25V;V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μA
VSDF	Diode forward voltage	I _{SD} =8A, V _{GS} = 0 V			1.3	V

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